

# Schottky barrier diode

## RB160L-60

### ●Applications

High frequency rectification  
For switching power supply.

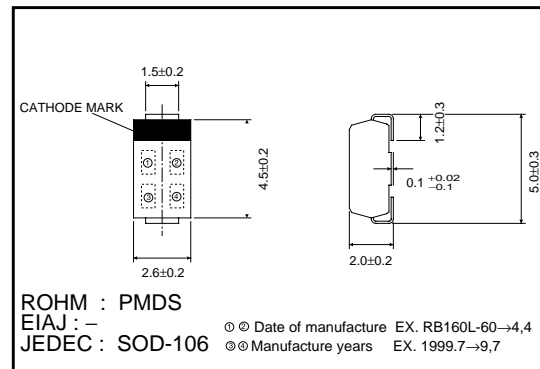
### ●Features

- 1) Compact power mold (PMDS)
- 2) Low  $V_F$ . ( $V_F=0.55V$  Typ. at 1A)
- 3) High reliability

### ●Construction

Silicon epitaxial Planar

### ●External dimensions (Units : mm)



### ●Absolute maximum ratings ( $T_a = 25^\circ C$ )

Parameter	Symbol	Limits	Unit
Peak reverse voltage	$V_{RM}$	60	V
DC reverse voltage	$V_R$	60	V
Mean rectifying current *	$I_O$	1	A
Peak forward surge current	$I_{FSM}$	30	A
Junction temperature	$T_J$	125	$^\circ C$
Storage temperature	$T_{stg}$	-40 ~ +125	$^\circ C$

\* When mounted on a PCBs board

### ●Electrical characteristics ( $T_a = 25^\circ C$ )

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$	-	-	0.58	V	$I_F = 1.0A$
Reverse current	$I_R$	-	-	0.5	mA	$V_R = 60V$

Diodes

●Electrical characteristic curves (Ta = 25°C)

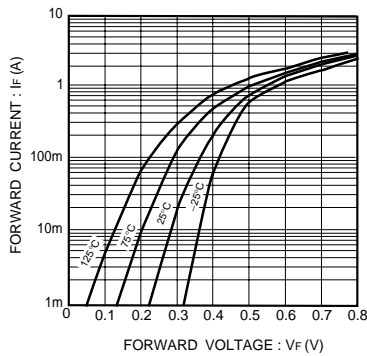


Fig.1 Forward characteristics

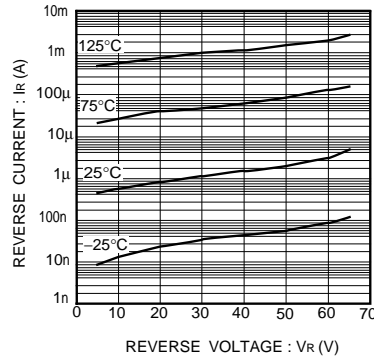


Fig.2 Reverse characteristics

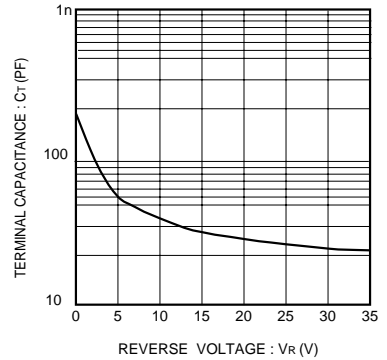


Fig.3 Capacitance between terminals characteristics

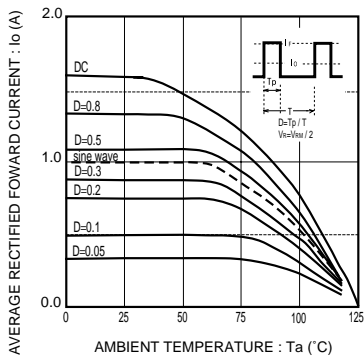


Fig.4 Derating curve (Io-Ta)

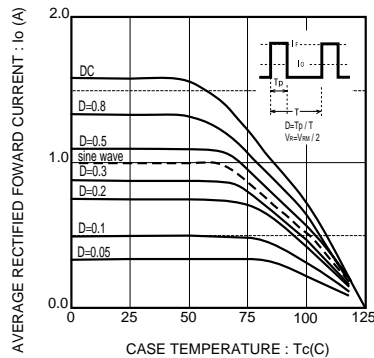


Fig.5 Derating curve (Io-Tc)